The first embodiment features the graded composition layer 104 provided between the base layer 103 and the active layer 105 to have a composition which is equal to the composition of the base layer 103 at the interface with the base layer 103 and to the composition of the active layer 105 at the interface with the active layer 105. If the film thickness of the graded composition layer 104 is about 5 nm to about 100 nm, the occurrence of an interface barrier can be suppressed. The composition of the graded composition layer 104 may be varied continuously or stepwise. Since light is emitted from the region of the graded composition layer 104 closer to the active layer 105, it is also possible to regard the region as a part of the active layer 105.

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Please replace the third full paragraph with the following:

As shown in FIG. 2, the graded composition layer 104 is provided between the active layer 105 and the base layer 103 to have a gradually varying composition which is equal to the composition of the active layer 105 at the interface with the active layer 105 and to the composition of the base layer 103 at the interface with the base layer 103. As a consequence, the interface barrier between the active layer 105 and the base layer 103 is reduced greatly compared with the semiconductor light-emitting device according to the conventional embodiment shown in FIG. 17. Even with a relatively low reverse voltage, therefore, the holes reaching the interface between the active layer 105 and the graded composition layer 104 swiftly move to the collector layer 103 so that the concentration of holes in the region of the active layer 105 closer to the base layer 103 is reduced significantly. As a result, the quantity of holes accumulated in the whole active layer 105 is also reduced, which achieves a significant reduction in the amount of residual light emitted from the semiconductor light-emitting device during the extinction period.

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IN THE CLAIMS:

Please amend claim 1 as follows:

Sub C1

1. (Amended) A semiconductor light-emitting device comprising:

first and second semiconductor layers each of a first conductivity type;

a third semiconductor layer of a second conductivity type provided between the first and second semiconductor layers;

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an active layer provided between the second and third semiconductor layers, the active layer emitting light with charge injected therein from the second and third semiconductor layers;